Preferred Device

NPN Silicon Transistor

Features

• Pb–Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	300	Vdc
Collector – Base Voltage	V _{CBO}	300	Vdc
Collector – Emitter Voltage	V _{CER}	300	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	Ι _C	100	mAdc
Total Power Dissipation up to $T_A = 25^{\circ}C$	PD	1.5	W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	R_{\thetaJA}	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

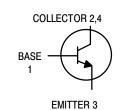
1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in².

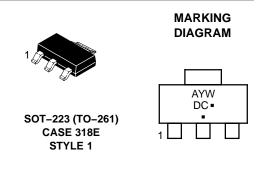


ON Semiconductor®

http://onsemi.com

NPN SILICON TRANSISTOR SURFACE MOUNT





Α = Assembly Location Υ = Year

- W
- = Work Week DC = Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BF720T1	SOT-223	1000 / Tape & Reel
BF720T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
BF720T3	SOT-223	4000 / Tape & Reel
BF720T3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	300	-	Vdc
Collector-Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	300	-	Vdc
Collector-Emitter Breakdown Voltage $(I_C = 100 \ \mu Adc, R_{BE} = 2.7 \ k\Omega)$	V _{(BR)CER}	300	-	Vdc
Emitter-Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	5.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = 200 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	10	nAdc
	I _{CER}		50 10	nAdc μAdc
ON CHARACTERISTICS	·			
DC Current Gain (I _C = 25 mAdc, V _{CE} = 20 Vdc)	h _{FE}	50	-	_
Collector-Emitter Saturation Voltage $(I_C = 30 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{CE(sat)}	-	0.6	Vdc
DYNAMIC CHARACTERISTICS			1	
Current–Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 35 MHz)	f _T	60	-	MHz
Feedback Capacitance $(V_{CE} = 30 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C _{re}	-	1.6	pF

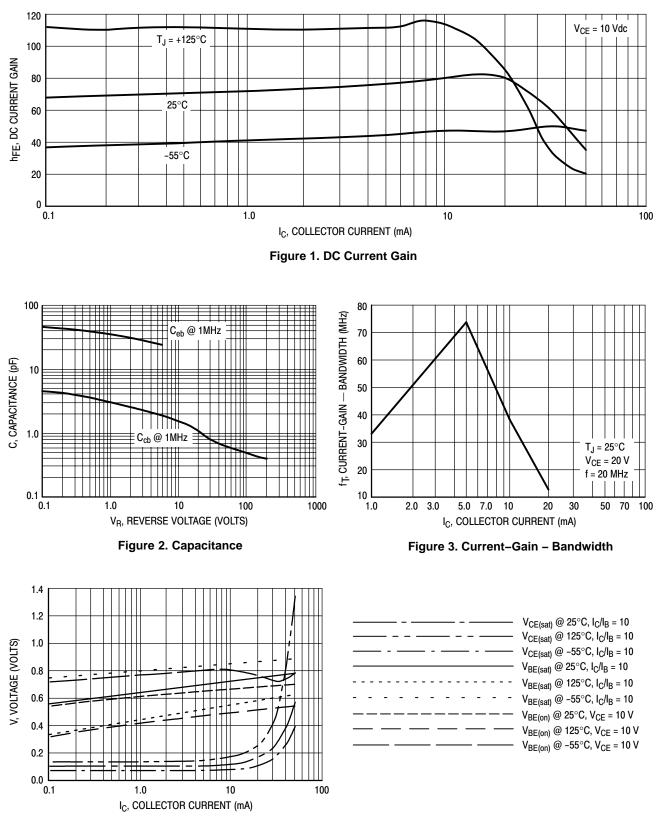
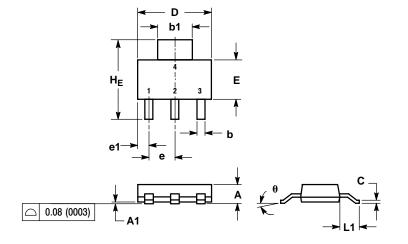


Figure 4. "ON" Voltages

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE L



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

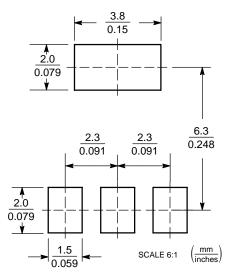
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
Е	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°



EMITTER
COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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